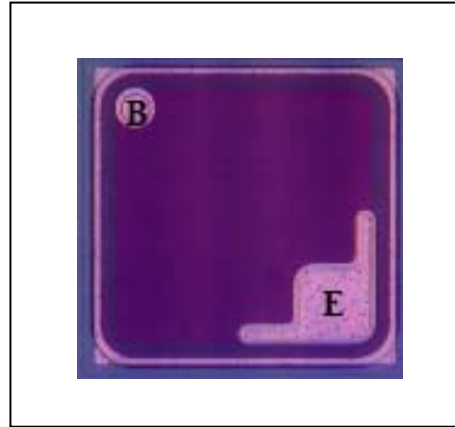


OPB0505P

Silicon Photo Transistor

1. Structure

- 1.1 Chip Size : 0.50mm X 0.50mm
- 1.2 Chip thickness : $180 \pm 20 \mu\text{m}$
- 1.3 Metallization : Top - Al, Bottom - Cr-Au
- 1.4 Passivation : Silicon Nitride
- 1.5 Bonding Pad Size
 - Emitter : $120 \times 120 \mu\text{m}$
 - Base : $60 \mu\text{m} \times 60 \mu\text{m}$



2. Electrical Characteristics

($T_a=25^\circ\text{C}$)

Parameter	Symbol	Min	Typ	Max	Unit	Condition
C-E Breakdown Voltage	V_{CE0}	30			V	$I_{CE}=100\mu\text{A}$
C-B Breakdown Voltage	V_{CBO}	30			V	$I_{CE}=10\mu\text{A}$
E-B Breakdown Voltage	V_{EBO}	5			V	$I_{CB}=10\mu\text{A}$
E-C Breakdown Voltage	V_{ECO}	5			V	$I_{EC}=10\mu\text{A}$
Collector Cut-Off Current	I_{CEO}			100	nA	$V_{CE}=20\text{V}$
C-E Saturation Voltage	V_{CES}			300	mV	$I_C=2\text{mA}, I_B=100\mu\text{A}$
DC Current Gain	h_{FE}	200			-	$V_{CE}=5\text{V}, I_C=2\text{mA}$

3. Maximum Ratings

($T_a=25^\circ\text{C}$)

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	30	V
Collector-Emitter Voltage	V_{CEO}	30	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	100	mA
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

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